

isc Silicon NPN Darlington Power Transistor

BDX33D

DESCRIPTION

- Collector-Emitter Sustaining Voltage-  
:  $V_{CEO(SUS)} = 120V(\text{Min})$
- High DC Current Gain  
:  $h_{FE} = 750(\text{Min}) @ I_C = 3A$
- Low Collector Saturation Voltage  
:  $V_{CE(sat)} = 2.5V(\text{Max.}) @ I_C = 3A$
- Complement to Type BDX34D

APPLICATIONS

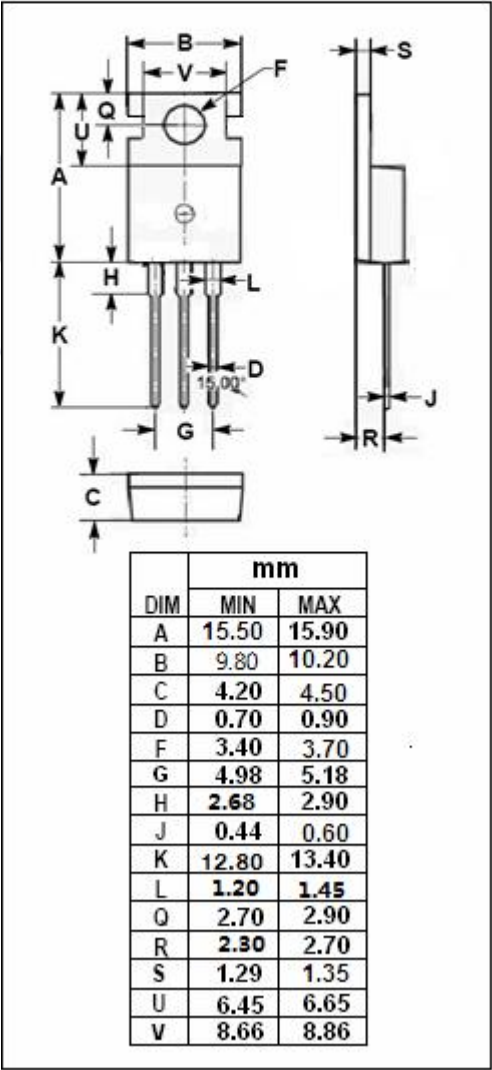
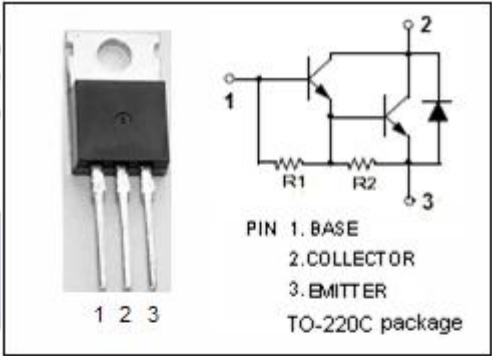
- Designed for general purpose amplifier and low speed switching applications.

ABSOLUTE MAXIMUM RATINGS( $T_a=25^{\circ}C$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	120	V
$V_{CEO}$	Collector-Emitter Voltage	120	V
$V_{EBO}$	Emitter-Base Voltage	5	V
$I_C$	Collector Current-Continuous	10	A
$I_{CM}$	Collector Current-Peak	15	A
$I_B$	Base Current-Continuous	0.25	A
$P_C$	Collector Power Dissipation @ $T_C=25^{\circ}C$	70	W
$T_J$	Junction Temperature	150	$^{\circ}C$
$T_{stg}$	Storage Temperature Range	-65~150	$^{\circ}C$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	1.78	$^{\circ}C/W$



**isc Silicon NPN Darlington Power Transistor****BDX33D****ELECTRICAL CHARACTERISTICS** **$T_C=25^{\circ}\text{C}$  unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEQ(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C=30\text{mA}; I_B=0$	120			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=3\text{A}; I_B=6\text{mA}$			2.5	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C=3\text{A}; V_{CE}=3\text{V}$			2.5	V
$I_{CBO}$	Collector Cutoff Current	$V_{CB}=120\text{V}; I_E=0$			0.2	mA
$I_{CEO}$	Collector Cutoff Current	$V_{CE}=60\text{V}; I_B=0$			0.5	mA
$I_{EBO}$	Emitter Cutoff Current	$V_{EB}=5\text{V}; I_C=0$			10	mA
$h_{FE}$	DC Current Gain	$I_C=3\text{A}; V_{CE}=3\text{V}$	750			